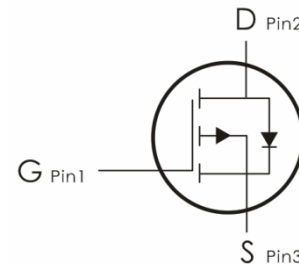
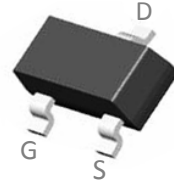


Description:

This P-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge. It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=-20V, I_D=-4.8A, R_{DS(ON)}<28m\Omega @V_{GS}=-4.5V$ (Typ: $22m\Omega$)
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.
- 6) MSL3



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DO2305A	2305A	SOT-23	3000 pcs/Reel

Absolute Maximum Ratings: ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current- $T_A=25^\circ\text{C}^1$	-4.8	A
	Continuous Drain Current- $T_A=100^\circ\text{C}^1$	-3.3	
I_{DM}	Drain Current – Pulsed ²	-19.2	
P_D	Power Dissipation	1.25	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	100	$^\circ\text{C}/\text{W}$

Electrical Characteristics: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-20	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=-20V$	---	---	-1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0A$	---	---	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-0.4	-0.6	-1	V
$R_{DS(on)}$	Drain-Source On Resistance ³	$V_{GS}=-4.5V, I_D=-4.1A$	---	22	28	$m\Omega$
		$V_{GS}=-2.5V, I_D=-3A$	---	28	36	
G_{FS}	Forward Transconductance	$V_{DS}=-5V, I_D=-2A$	---	6	---	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=-4, V_{GS}=0V, f=1MHz$	---	900	---	pF
C_{oss}	Output Capacitance		---	290	---	
C_{rss}	Reverse Transfer Capacitance		---	190	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DS}=-10V, I_D=-3.3A,$ $R_{ENG}=1\Omega, V_{GS}=-4.5V$	---	12	---	ns
t_r	Rise Time		---	35	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	30	---	ns
t_f	Fall Time		---	10	---	ns
Q_g	Total Gate Charge	$V_{GS}=-4.5V, V_{DS}=-4$	---	8.8	---	nC
Q_{gs}	Gate-Source Charge	$I_D=-4.1, V_{DS}=-4V$	---	1.2	---	nC
Q_{gd}	Gate-Drain "Miller" Charge		---	1.6	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Source-Drain Diode Forward Voltage	$V_{GS}=0V, I_F=1.6A$	---	---	-1.2	V
I_S	Continuous Drain Current	$V_D=V_G=0V$	---	---	-4	A
I_{SM}	Pulsed Drain Current		---	---	-16	A

Notes:

1. omputed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Characteristics: ($T_A=25^\circ C$ unless otherwise noted)

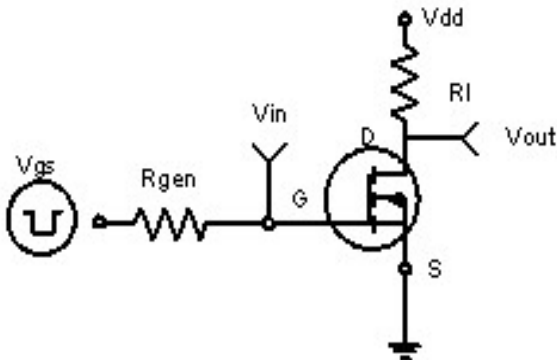


Figure 1: Switching Test Circuit

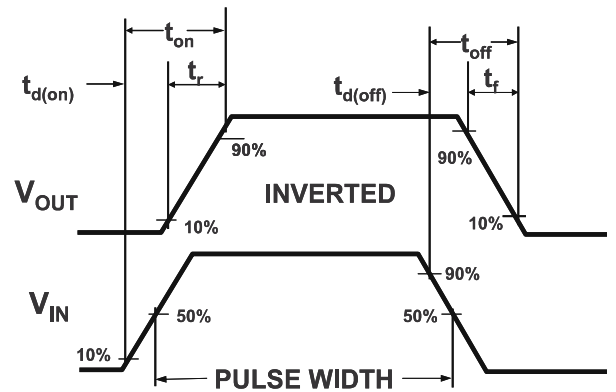


Figure 2: Switching Waveforms

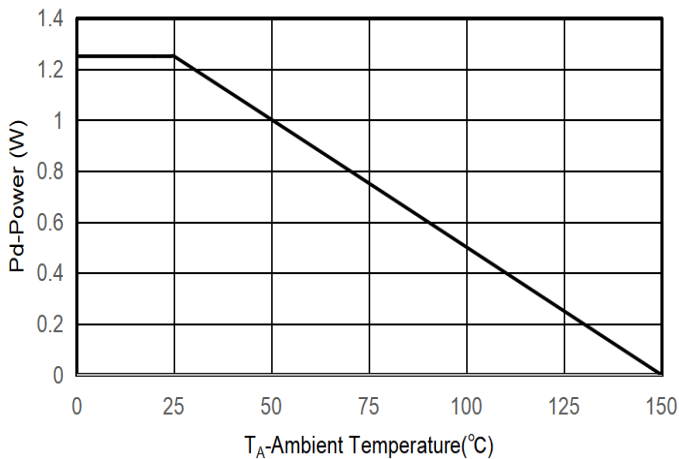


Figure 3 Power Dissipation

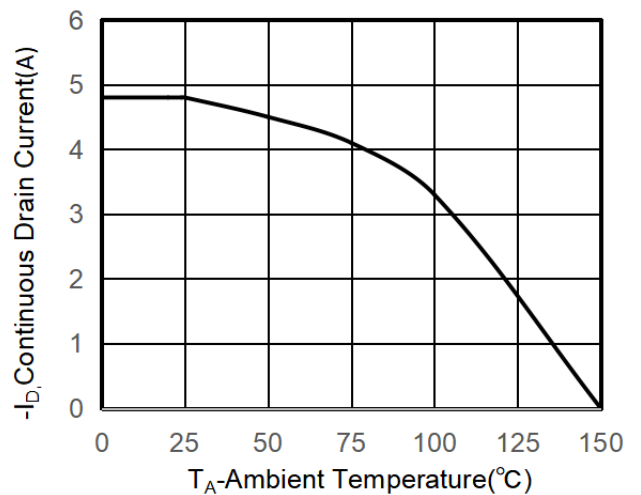


Figure 4 Drain Current

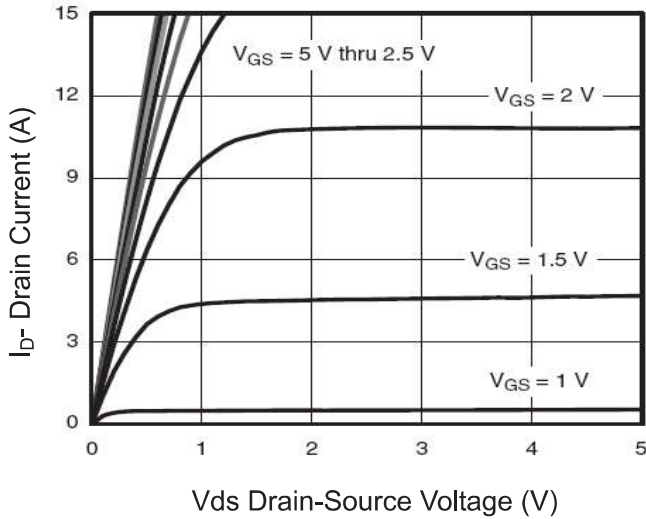


Figure 5 Output Characteristics

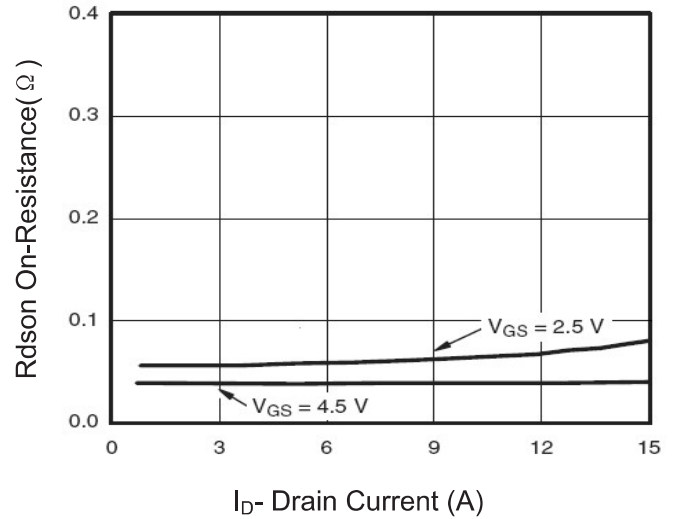


Figure 6 Drain-Source On-Resistance

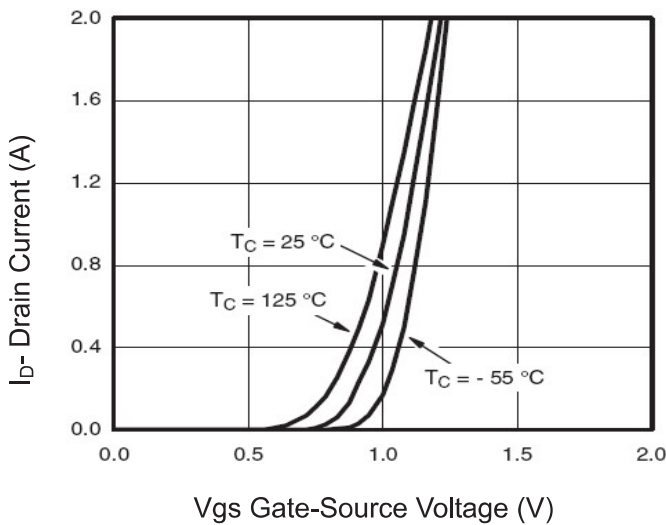


Figure 7 Transfer Characteristics

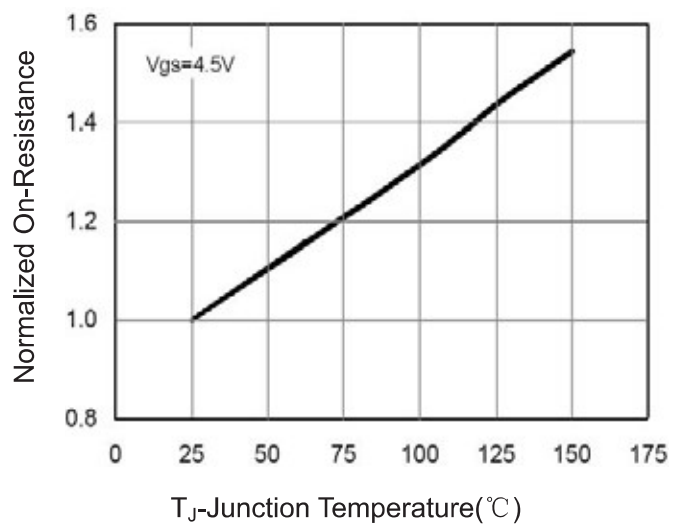


Figure 8 Drain-Source On-Resistance

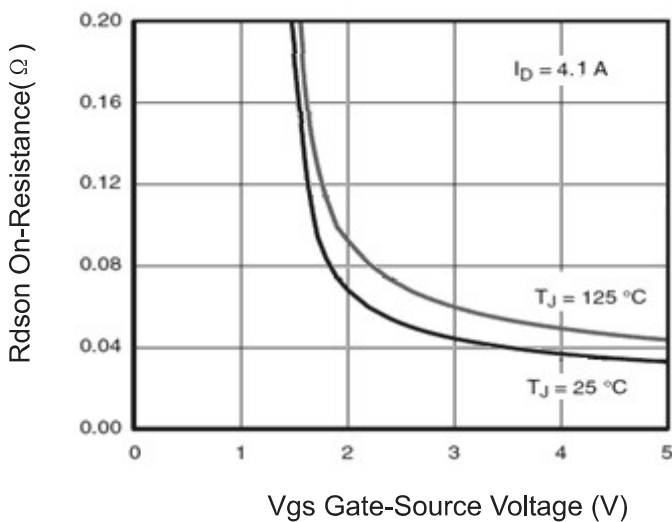


Figure 9 Rdson vs Vgs

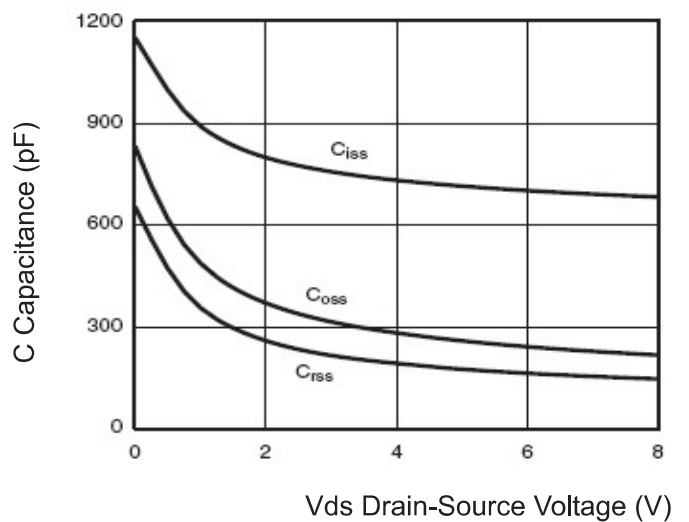


Figure 10 Capacitance vs Vds

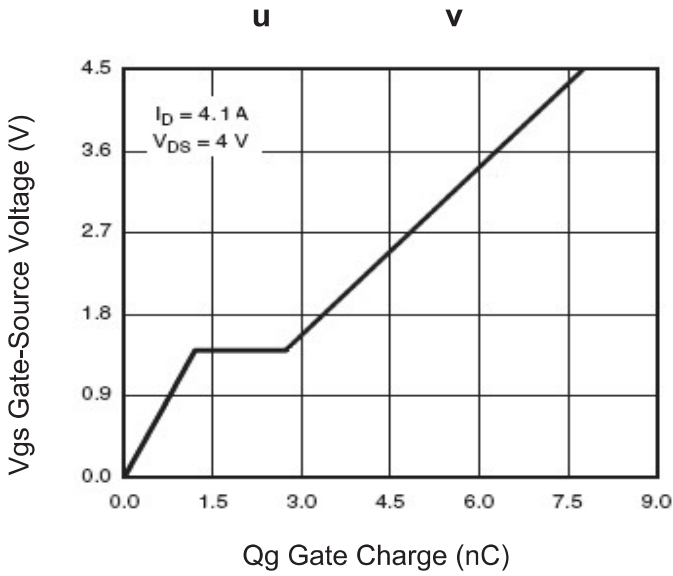


Figure 11 Gate Charge

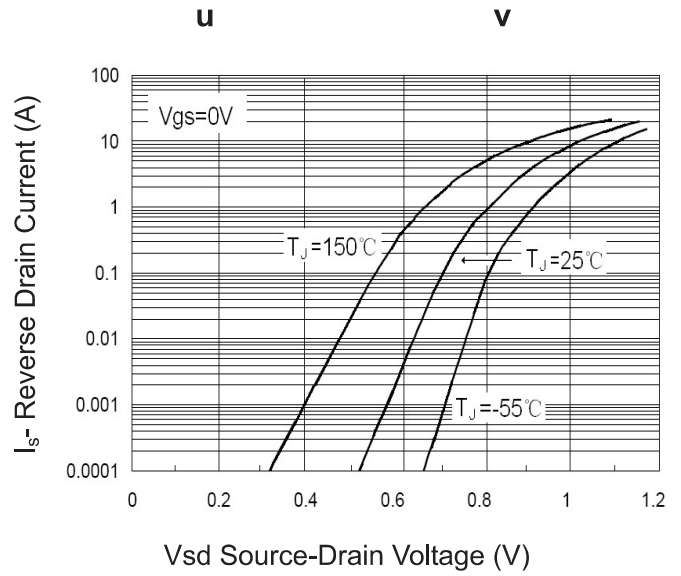


Figure 12 Source-Drain Diode Forward

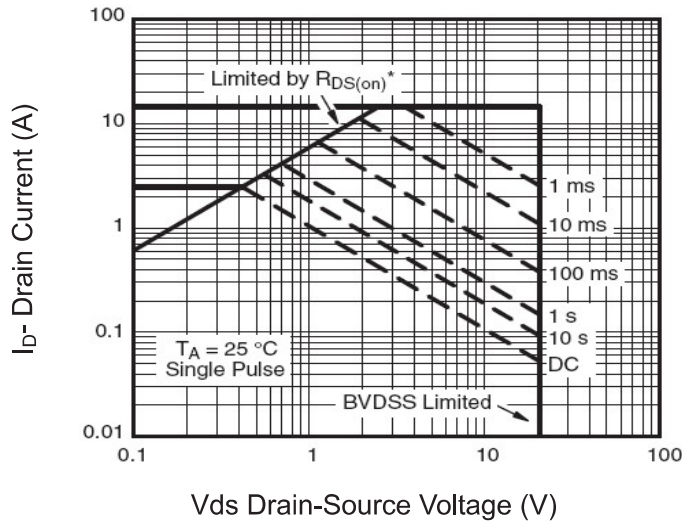


Figure 13 Safe Operation Area

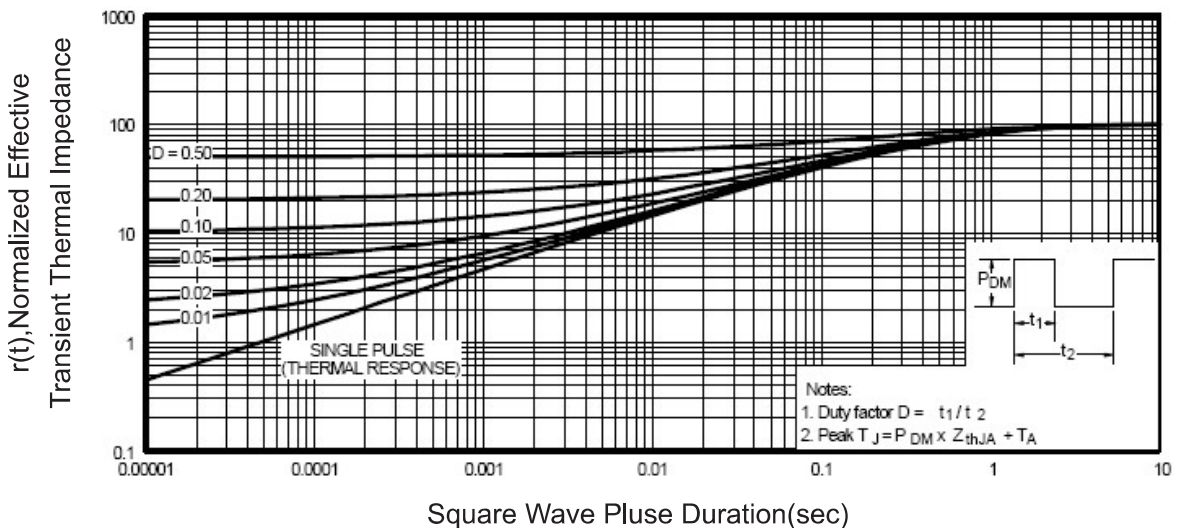
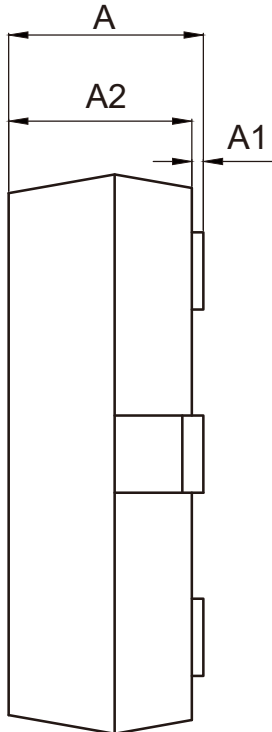
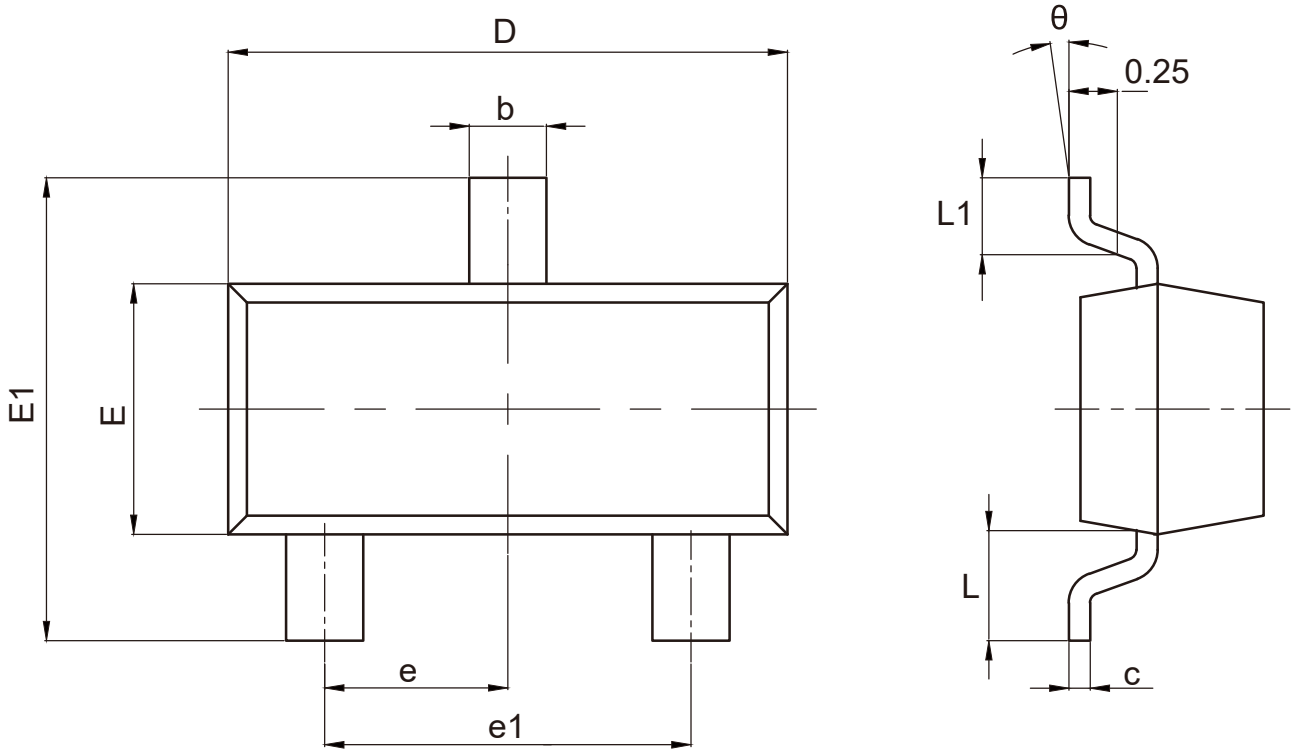


Figure 14 Normalized Maximum Transient Thermal Impedance

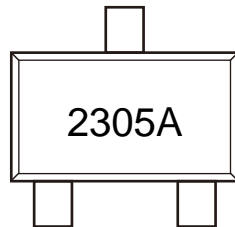
SOT-23 Package Outline Data



COMMON DIMENSIONS			
CUNITS MEASURE=MILLIMETER			
SYMBOL	MIN	NOM	MAX
A	0.900	--	1.150
A1	0.000	--	0.100
A2	0.900	--	1.050
c	0.100	--	0.200
b	0.300	0.400	0.500
D	2.800	2.900	3.000
E	1.200	--	1.400
E1	2.250	--	2.550
e	0.950TYP		
e1	1.800	1.900	2.000
L	0.550REF		
L1	0.300	0.400	0.500
θ	0°	--	8°

Unit:mm

Marking Information:



Previous Version

Version	Date	Subjects (major changes since last revision)
2.1	2025-09-18	Release of final version

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